



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
30V	58mΩ @ V <sub>GS</sub> = 8V	4.6A
	62mΩ @ V <sub>GS</sub> = 4.5V	4.4A

## Description

This new generation MOSFET is designed to minimize the footprint in handheld and mobile application. It can be used to replace many small signals MOSFET with as really small footprint.

## Applications

- Battery Management
- Load Switch
- Battery Protection
- Handheld and Mobile Application

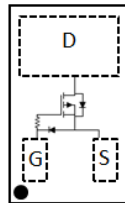
## Features and Benefits

- Low Q<sub>g</sub> & Q<sub>gd</sub>
- Small Footprint
- Low Profile 0.20mm Height

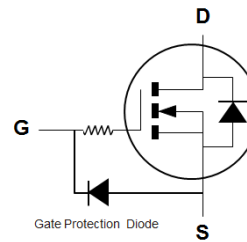
## Mechanical Data

- Case: X4-DSN1006-3
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 (E4)
- Weight: 0.00029 grams (Approximate)

X4-DSN1006-3 (Type C)



Top View



Equivalent Circuit

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	12	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 8V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	4.6	A
		T <sub>A</sub> = +70°C		3.7	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	4.4	A
		T <sub>A</sub> = +70°C		3.5	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	20	A

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	1.12	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	113.4	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	1.88	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	66.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	100	nA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	50	nA	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.65	0.85	1.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DSS(ON)</sub>	—	47	58	mΩ	V <sub>GS</sub> = 8V, I <sub>D</sub> = 0.5A
		—	54	62		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.5A
		—	71	110		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 0.5A
		—	104	160		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 0.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	0.9	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.5A
Reverse Recovery Charge	Q <sub>RR</sub>	—	2.4	—	nC	V <sub>DD</sub> = 15V, I <sub>F</sub> = 0.5A,
Reverse Recovery Time	t <sub>RR</sub>	—	7.1	—	ns	di/dt = 300A/μs
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	126	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	81	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	4.5	—		
Series Gate Resistance	R <sub>g</sub>	—	3.7	—	Ω	f = 1MHz, V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V
Total Gate Charge	Q <sub>g</sub>	—	1.4	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 0.5A
Gate-Source Charge	Q <sub>gs</sub>	—	0.2	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	0.2	—		
Gate Charge at V <sub>TH</sub>	Q <sub>g(TH)</sub>	—	0.2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.3	—	ns	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, R <sub>g</sub> = 2Ω, I <sub>D</sub> = 0.5A
Turn-On Rise Time	t <sub>r</sub>	—	1.9	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	9.1	—		
Turn-Off Fall Time	t <sub>f</sub>	—	5.1	—		

- Notes:
- Device mounted on FR-4 material with 1inch<sup>2</sup> (6.45cm<sup>2</sup>), 2-oz. (0.071mm thick) Cu.
  - Repetitive rating, pulse width limited by junction temperature.
  - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

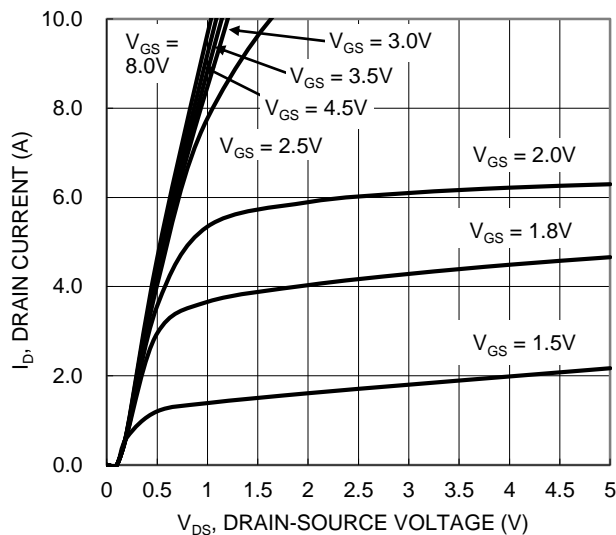


Figure 1. Typical Output Characteristic

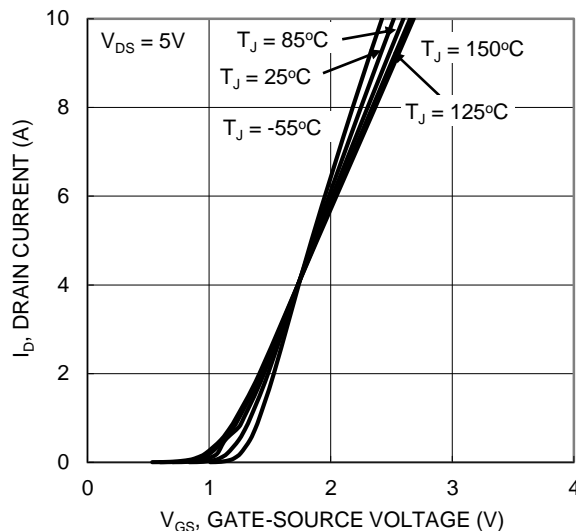


Figure 2. Typical Transfer Characteristic

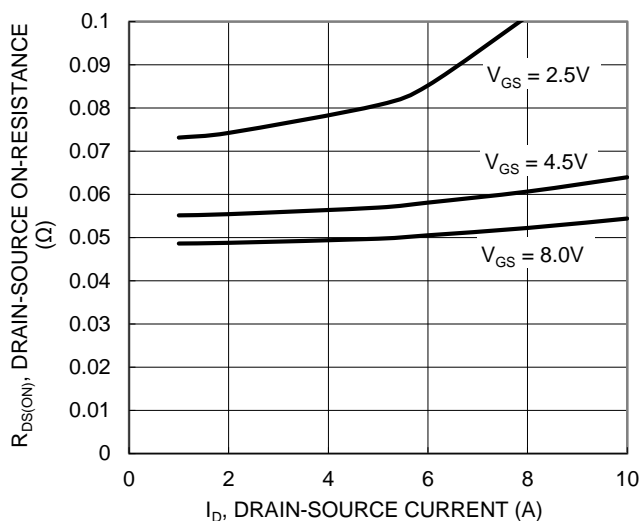


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

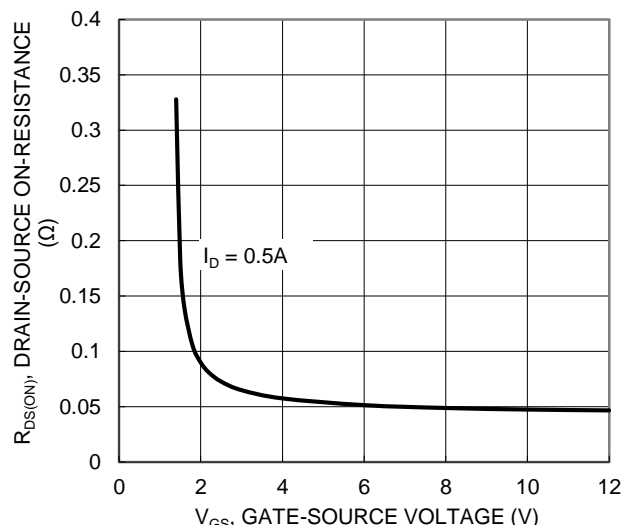


Figure 4. Typical Transfer Characteristic

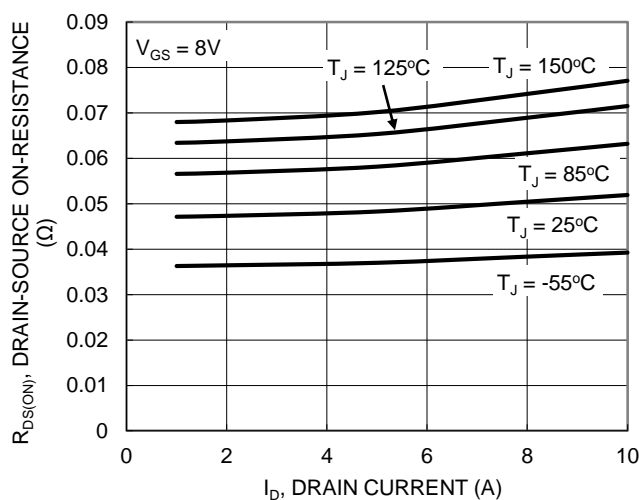


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

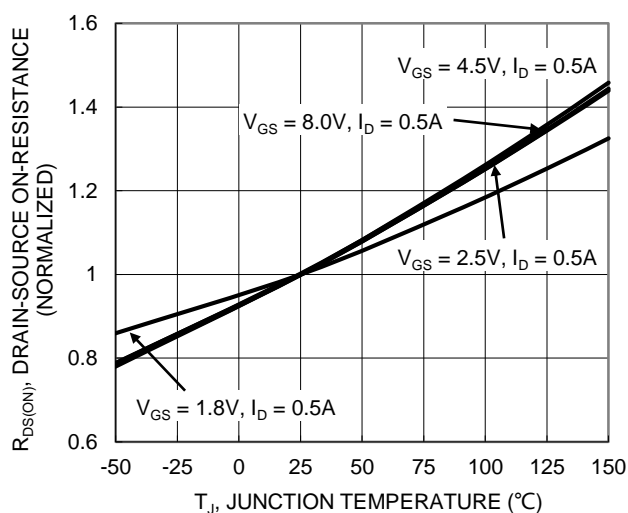


Figure 6. On-Resistance Variation with Junction Temperature

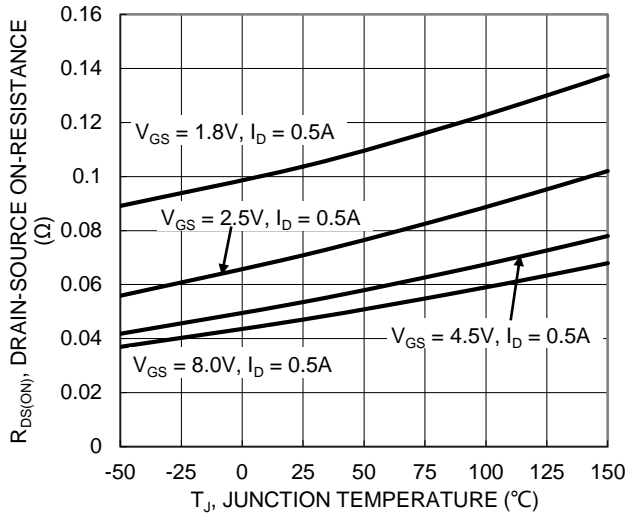


Figure 7. On-Resistance Variation with Junction Temperature

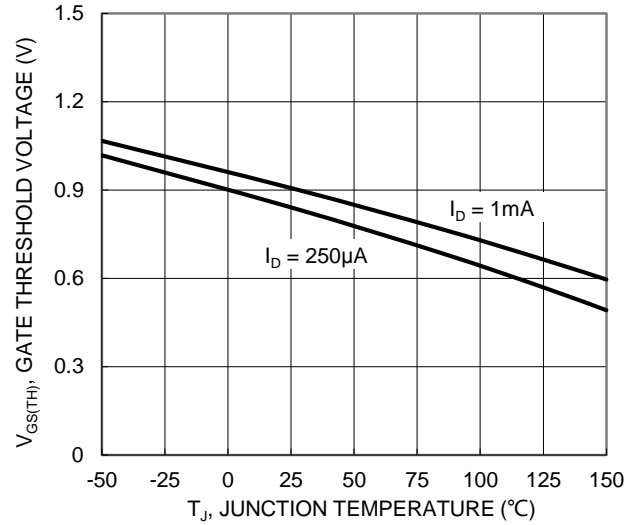


Figure 8. Gate Threshold Variation vs. Junction Temperature

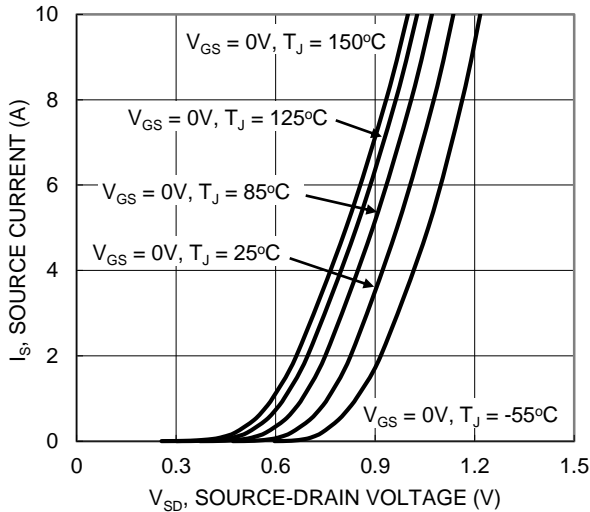


Figure 9. Diode Forward Voltage vs. Current

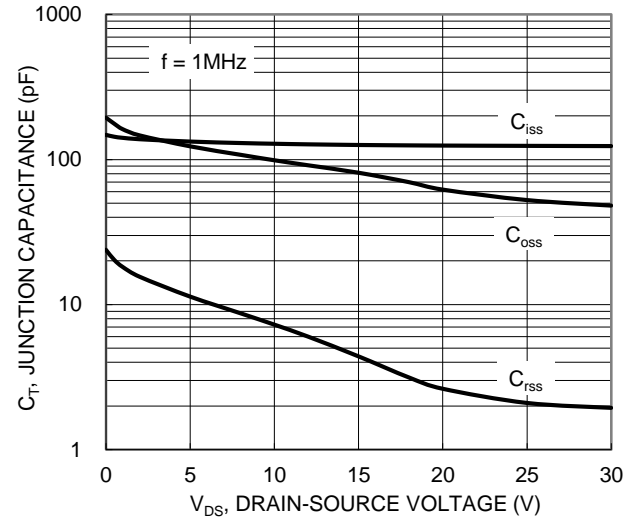


Figure 10. Typical Junction Capacitance

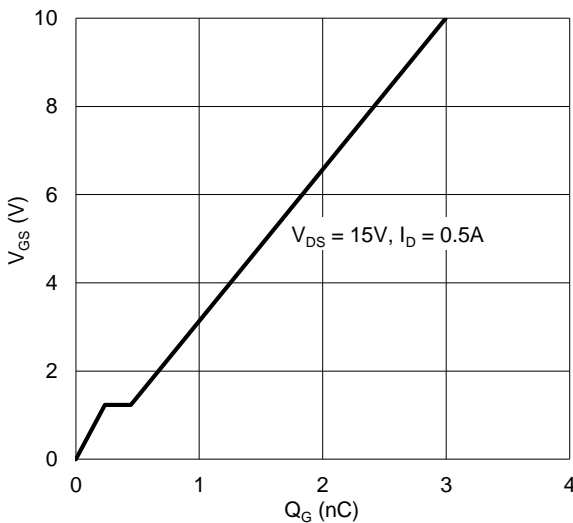


Figure 11. Gate Charge

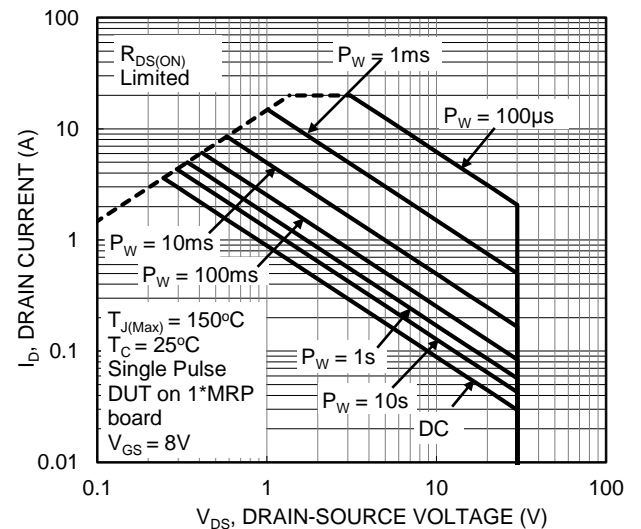


Figure 12. SOA, Safe Operation Area

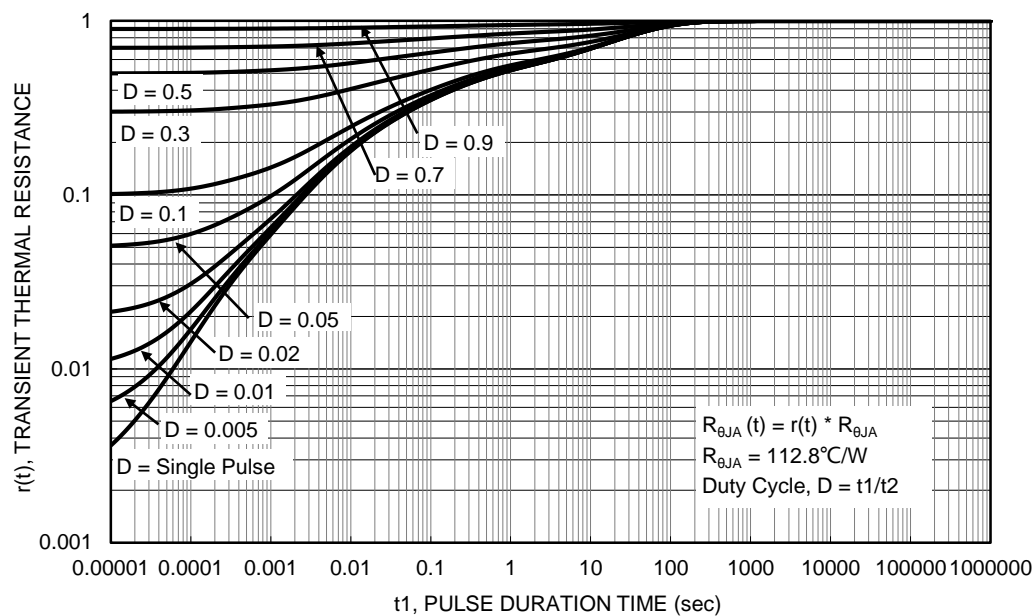
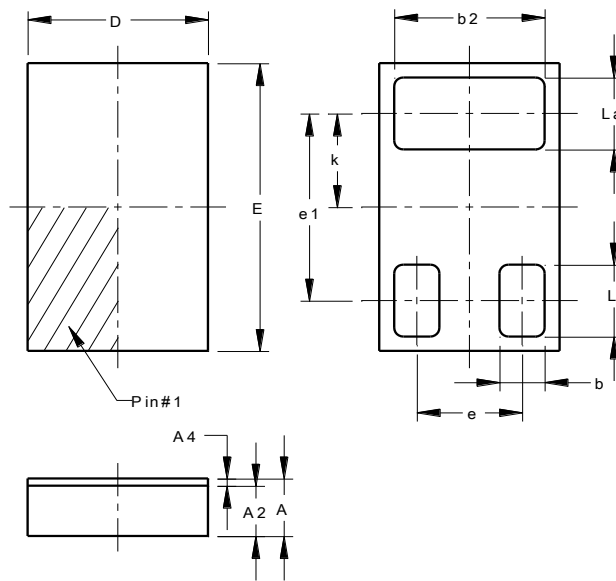


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

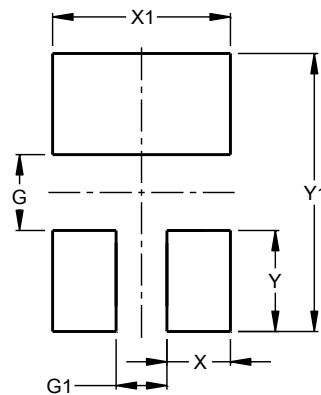
X4-DSN1006-3 (Type C)



X4-DSN1006-3 (Type C)			
Dim	Min	Max	Typ
A	0.18	0.22	0.20
A2	--	--	0.175
A4	--	--	0.025
b	0.14	0.16	0.15
b2	0.49	0.51	0.50
D	0.56	0.64	0.60
E	0.96	1.04	1.00
e	--	--	0.35
e1	--	--	0.65
k	--	--	0.325
L	0.24	0.26	0.25
La	0.24	0.26	0.25
All Dimensions in mm			

## Suggested Pad Layout

X4-DSN1006-3 (Type C)



Dimensions	Value (in mm)
G	0.40
G1	0.20
X	0.15
X1	0.50
Y	0.25
Y1	0.90